



3DG112



NPN Silicon High Frequency Low Power Transistor

Features:

1. Using epitaxy planar technology structure. High working frequency. Metallic packaging.
2. Small volume, light weight, easy installation.
3. Use for high frequency oscillation, high frequency small signal amplification, low power source adjustment circuit.
4. Quality Class: GS, G. Implementation of standards: QZJ840611

TECHNICAL DATA:

(Ta = 25°C)

Parameter name	Symbols	Unit	Specifications				Test Condition
			A	B	C	D	
Total Dissipation	P _{tot}	mW	300				Ta=25°C
Max. Collector Current	I _{CM}	mA	50				
Junction Temperature	T _{jm}	°C	175				
Storage Temperature	T _{stg}	°C	-55~+175				
C-B Breakdown Voltage	V _{(BR)CBO}	V	20	40	20	40	I _C =0.1mA
C-E Breakdown Voltage	V _{(BR)CEO}	V	15	30	15	30	
E-B Breakdown Voltage	V _{(BR)EBO}	V	4				I _E =0.1mA
Collector- Emitter Saturation Voltage Drop	V _{CE(sat)}	V	0.35				I _C =10mA I _B =1mA
Base- Emitter Saturation Voltage Drop	V _{BE(sat)}	V	1.0				
C-B Leakage Current	I _{CBO}	uA	0.1				V _{CB} =10V
C-E Leakage Current	I _{CEO}	uA	0.1				V _{CE} =10V
E-B Leakage Current	I _{EBO}	uA	0.1				V _{EB} =1.5V
DC Current Gain	h _{FE}		25~270				V _{CE} =10V, I _C =10mA
Transition frequency	f _T	MHz	500	500	700	700	V _{CE} =10V, I _C =10mA f=100MHz

h_{FE} Colored:

Color	Orange	Yellow	Green	Blue	Purple	Gray
h _{FE}	25~40	40~55	55~80	80~120	120~180	180~270

Outline and Dimensions: